Part Number	Customer

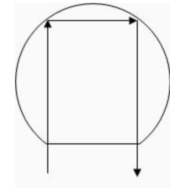
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Overall Thickness	431.00 +/- 10.00 µm	ADE, 100%
	5.0	LPDs > 0.3um	<30	Tencor Particle counter
	6.0	Frontsurface condition	Polished, roughness <5A	Guaranteed by process
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0	Bow	<60.00µm	ADE to ASTM F534, 100%
	9.0	Warp	<60.00µm	
	10.0	Edge Chips	0	Bright Light, 100%
	11.0	Edge Exclusion	5mm	
	12.0	Lasermarking	On wafer BACKSIDE	Guaranteed by process
HandleSilicon	13.0	Handle Growth Method	CZ	Wafer Vendor
	14.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	15.0	Handle Thickness	400.00 +/- 9.00 µm	ADE, 100%
	16.0	Handle Doping Type	P	Wafer Vendor
	17.0	Handle Dopant	Boron	Wafer Vendor
	18.0	Handle Resistivity	8 ~ 12 Ohmcm	Wafer Vendor
	19.0	Backside Finish	Polished with lasermark and oxide	Wafer Vendor
BuriedOxide	20.0	Oxide Type	Thermal	
	21.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	22.0	Oxide formed on	Handle	
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	25.0	Nominal Thickness	30.00 +/- 0.50 µm	Filmetrics, 100% 9-Pt (note3)
	26.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Phosphorous	Wafer Vendor
	29.0	Device Resistivity	3 ~ 5 ohm-cm	Wafer Vendor
	30.0	Voids	none	IR Inspection, 100%
	31.0	Scratches	0	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)
	33.0	Front Surface	Polished, roughness <5A.	Guaranteed by process

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

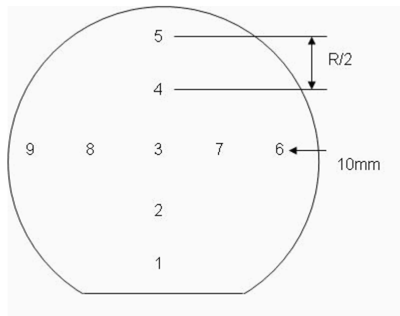
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information